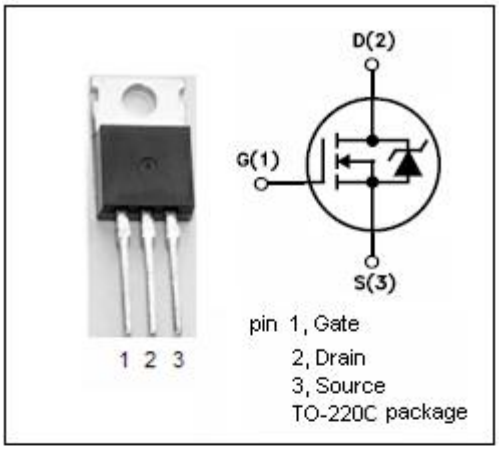
isc N-Channel Mosfet Transistor BUZ10



- **FEATURES**
- Drain Current –I_D=23A@ T_C=25℃
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 0.07Ω (Max)
- 175℃ operating temperature
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

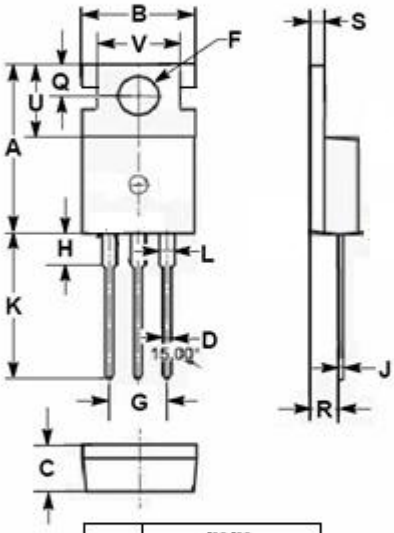
- **DESCRIPTION**
- High current , high speed switching
- Solenoid and relay drivers
- DC-DC & DC-AC converters

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	50	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	23	A
I_{DM}	Drain Current-Single Plused	92	A
P_{tot}	Total Dissipation@TC=25℃	75	W
T_j	Max. Operating Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-65~175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.0	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 0.25mA	50		V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 1mA	2.1	4	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 10V; I_D= 14A		0.07	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 50V; V_{GS}= 0		1	uA
V_{SD}	Diode Forward Voltage	I_F= 46A; V_{GS}= 0		1.9	V
Gfs	Forward Transconductance	V_{DS}= 25V； I_D=14A	6.0		S